

General Description

The ICS844246DI is a Crystal-to-LVDS Clock Synthesizer/Fanout Buffer designed for Fibre Channel frequencies and Gigabit Ethernet applications. The output frequency can be set using the frequency select pins and a 25MHz crystal for Ethernet frequencies, or a 26.5625MHz crystal for a Fibre Channel. The low phase noise characteristics of the ICS844246DI make it an ideal clock for these demanding applications.

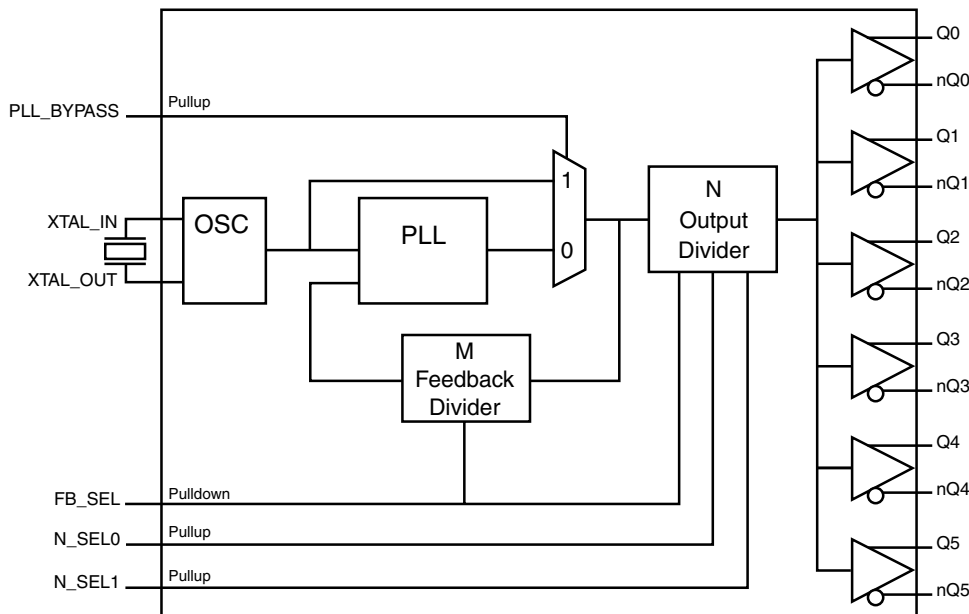
Features

- Six LVDS output pairs
- Crystal oscillator interface
- Output frequency range: 53.125MHz to 333.3333MHz
- Crystal input frequency range: 25MHz to 33.3333MHz
- RMS phase jitter @ 125MHz, using a 25MHz crystal (1.875MHz - 20MHz): 0.416ps (typical)
- Full 3.3V or mixed 3.3V core, 2.5V output supply modes
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Select Function Table

| Inputs | | | Function | | |
|--------|--------|--------|----------|----------|---------------|
| FB_SEL | N_SEL1 | N_SEL0 | M Divide | N Divide | M/N |
| 0 | 0 | 0 | 20 | 2 | 10 |
| 0 | 0 | 1 | 20 | 4 | 5 |
| 0 | 1 | 0 | 20 | 5 | 4 |
| 0 | 1 | 1 | 20 | 8 | 2.5 (default) |
| 1 | 0 | 0 | 24 | 3 | 8 |
| 1 | 0 | 1 | 24 | 4 | 6 |
| 1 | 1 | 0 | 24 | 6 | 4 |
| 1 | 1 | 1 | 24 | 12 | 2 |

Block Diagram



Pin Assignment

| | | | |
|------------|----|----|----------|
| VDD0 | 1 | 24 | Q3 |
| VDD0 | 2 | 23 | nQ3 |
| nQ2 | 3 | 22 | Q4 |
| Q2 | 4 | 21 | nQ4 |
| nQ1 | 5 | 20 | Q5 |
| Q1 | 6 | 19 | nQ5 |
| nQ0 | 7 | 18 | N_SEL1 |
| Q0 | 8 | 17 | GND |
| PLL_BYPASS | 9 | 16 | GND |
| VDDA | 10 | 15 | N_SEL0 |
| VDD | 11 | 14 | XTAL_OUT |
| FB_SEL | 12 | 13 | XTAL_IN |

ICS844246DI
24-Lead TSSOP, E-Pad
4.4mm x 7.8mm x 0.925mm
package body
G Package
Top View

Table 1. Pin Descriptions

| Number | Name | Type | | Description |
|----------|----------------------|--------|----------|--|
| 1, 2 | V _{DDO} | Power | | Output supply pins. |
| 3, 4 | nQ2, Q2 | Output | | Differential output pair. LVDS interface levels. |
| 5, 6 | nQ1, Q1 | Output | | Differential output pair. LVDS interface levels. |
| 7, 8 | nQ0, Q0 | Output | | Differential output pair. LVDS interface levels. |
| 9 | PLL_BYPASS | Input | Pullup | Selects between the PLL and crystal inputs as the input to the dividers. When LOW, selects PLL. When HIGH, bypasses the PLL. LVCMOS / LVTTTL interface levels. |
| 10 | V _{DDA} | Power | | Analog supply pin. |
| 11 | V _{DD} | Power | | Core supply pin. |
| 12 | FB_SEL | Input | Pulldown | Feedback frequency select pin. LVCMOS/LVTTTL interface levels. |
| 13 14 | XTAL_IN, XTAL_OUT | Input | | Crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output. |
| 15, 18 | N_SEL0, N_SEL1 | Input | Pullup | Output frequency select pin. LVCMOS/LVTTTL interface levels. |
| 16, 17 | GND | Power | | Power supply ground. |
| 19, 20 | nQ5, Q5 | Output | | Differential output pair. LVDS interface levels. |
| 21, 22 | nQ4, Q4 | Output | | Differential output pair. LVDS interface levels. |
| 23, 24 | nQ3, Q3 | Output | | Differential output pair. LVDS interface levels. |

NOTE: *Pullup and Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

Table 2. Pin Characteristics

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------------|-------------------------|-----------------|---------|---------|---------|-------|
| C _{IN} | Input Capacitance | | | 4 | | pF |
| R _{PULLUP} | Input Pullup Resistor | | | 51 | | kΩ |
| R _{PULLDOWN} | Input Pulldown Resistor | | | 51 | | kΩ |

Function Tables

Table 3. Crystal Function Table

| Inputs | | | | Function | | | Output Frequency (MHz) |
|------------|--------|--------|--------|----------|-----------|----|------------------------|
| XTAL (MHz) | FB_SEL | N_SEL1 | N_SEL0 | M | VCO (MHz) | N | |
| 25 | 0 | 0 | 0 | 20 | 500 | 2 | 250 |
| 25 | 0 | 0 | 1 | 20 | 500 | 4 | 125 |
| 25 | 0 | 1 | 0 | 20 | 500 | 5 | 100 |
| 25 | 0 | 1 | 1 | 20 | 500 | 8 | 62.5 |
| 25 | 1 | 0 | 0 | 24 | 600 | 3 | 200 |
| 25 | 1 | 0 | 1 | 24 | 600 | 4 | 150 |
| 25 | 1 | 1 | 0 | 24 | 600 | 6 | 100 |
| 25 | 1 | 1 | 1 | 24 | 600 | 12 | 50 |
| 26.5625 | 0 | 1 | 0 | 20 | 531.25 | 5 | 106.25 |
| 26.5625 | 1 | 0 | 0 | 24 | 637.5 | 3 | 212.5 |
| 26.5625 | 1 | 0 | 1 | 24 | 637.5 | 4 | 159.375 |
| 26.5625 | 1 | 1 | 0 | 24 | 637.5 | 6 | 106.25 |
| 26.5625 | 1 | 1 | 1 | 24 | 637.5 | 12 | 53.125 |
| 30 | 0 | 0 | 0 | 20 | 600 | 2 | 300 |
| 30 | 0 | 0 | 1 | 20 | 600 | 4 | 150 |
| 30 | 0 | 1 | 0 | 20 | 600 | 5 | 120 |
| 30 | 0 | 1 | 1 | 20 | 600 | 8 | 75 |
| 31.25 | 0 | 0 | 0 | 20 | 625 | 2 | 312.5 |
| 31.25 | 0 | 0 | 1 | 20 | 625 | 4 | 156.25 |
| 31.25 | 0 | 1 | 0 | 20 | 625 | 5 | 125 |
| 31.25 | 0 | 1 | 1 | 20 | 625 | 8 | 78.125 |
| 33.3333 | 0 | 0 | 0 | 20 | 666.6667 | 2 | 333.3333 |
| 33.3333 | 0 | 0 | 1 | 20 | 666.6667 | 4 | 166.6667 |
| 33.3333 | 0 | 1 | 0 | 20 | 666.6667 | 5 | 133.3333 |
| 33.3333 | 0 | 1 | 1 | 20 | 666.6667 | 8 | 83.3333 |

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

| Item | Rating |
|--|--|
| Supply Voltage, V_{DD} | 4.6V |
| Inputs, V_I XTAL_IN Other Inputs | 0V to V_{DD} -0.5V to $V_{DD} + 0.5V$ |
| Outputs, I_O (LVDS) Continuous Current Surge Current | 10mA 15mA |
| Package Thermal Impedance, θ_{JA} | 32.1°C/W (0 mps) |
| Storage Temperature, T_{STG} | -65°C to 150°C |

DC Electrical Characteristics

Table 4A. LVDS Power Supply DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|-----------------|-----------------|---------|----------|-------|
| V_{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDA} | Analog Supply Voltage | | $V_{DD} - 0.10$ | 3.3 | V_{DD} | V |
| V_{DDO} | Output Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| I_{DD} | Power Supply Current | | | | 170 | mA |
| I_{DDA} | Analog Supply Current | | | | 10 | mA |
| I_{DDO} | Output Supply Current | | | | 100 | mA |

Table 4B. LVDS Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------|-----------------------|-----------------|-----------------|---------|----------|-------|
| V_{DD} | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V_{DDA} | Analog Supply Voltage | | $V_{DD} - 0.10$ | 3.3 | V_{DD} | V |
| V_{DDO} | Output Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| I_{DD} | Power Supply Current | | | | 165 | mA |
| I_{DDA} | Analog Supply Current | | | | 10 | mA |
| I_{DDO} | Output Supply Current | | | | 98 | mA |

Table 4C. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 5\%$ $V_{DDO} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------|--------------------|---------------------------|---|---------|----------------|---------|
| V_{IH} | Input High Voltage | $V_{DD} = 3.465V$ | 2 | | $V_{DD} + 0.3$ | V |
| V_{IL} | Input Low Voltage | $V_{DD} = 3.465V$ | -0.3 | | 0.8 | V |
| I_{IH} | Input High Current | N_SEL[1:0], PLL_BYPASS | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | 5 | μA |
| | | FB_SEL | $V_{DD} = V_{IN} = 3.465V$ or $2.625V$ | | 150 | μA |
| I_{IL} | Input Low Current | N_SEL[1:0], PLL_BYPASS | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -150 | | μA |
| | | FB_SEL | $V_{DD} = 3.465V$ or $2.625V$, $V_{IN} = 0V$ | -5 | | μA |

Table 4D. LVDS DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|-----------------------------|-----------------|---------|---------|---------|-------|
| V_{OD} | Differential Output Voltage | | 247 | | 454 | mV |
| ΔV_{OD} | V_{OD} Magnitude Change | | | | 100 | mV |
| V_{OS} | Offset Voltage | | 1.10 | | 1.50 | V |
| ΔV_{OS} | V_{OS} Magnitude Change | | | | 120 | mV |

Table 5. Crystal Characteristics

| Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------------------------|-----------------|-------------|---------|---------|----------|
| Mode of Oscillation | | Fundamental | | | |
| Frequency | | 25 | | 33.333 | MHz |
| Equivalent Series Resistance (ESR) | | | | 50 | Ω |
| Shunt Capacitance | | | | 7 | pF |

NOTE: Characterized using an 18pF parallel resonant crystal.

AC Electrical Characteristics

Table 6. LVDS AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 3.3V \pm 5\%$ or $2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ to 85°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|----------------------|--------------------------------------|--|---------|---------|---------|-------|
| f_{OUT} | Output Frequency | PLL_BYPASS = 0 | 50 | | 333.33 | MHz |
| | | In bypass mode with 25MHz Crystal, PLL_BYPASS = 1 (default) | | 3.125 | | MHz |
| $f_{jit}(\emptyset)$ | RMS Phase Jitter (Random); NOTE 1 | 125MHz, Integration Range: 1.875MHz – 20MHz | | 0.416 | 0.560 | ps |
| $t_{sk(o)}$ | Output Skew; NOTE 2, 3 | | | | 45 | ps |
| t_R / t_F | Output Rise/Fall Time | 20% to 80% | 220 | | 380 | ps |
| odc | Output Duty Cycle | | 45 | | 55 | % |
| t_{LOCK} | PLL Lock Time | | | | 25 | ms |

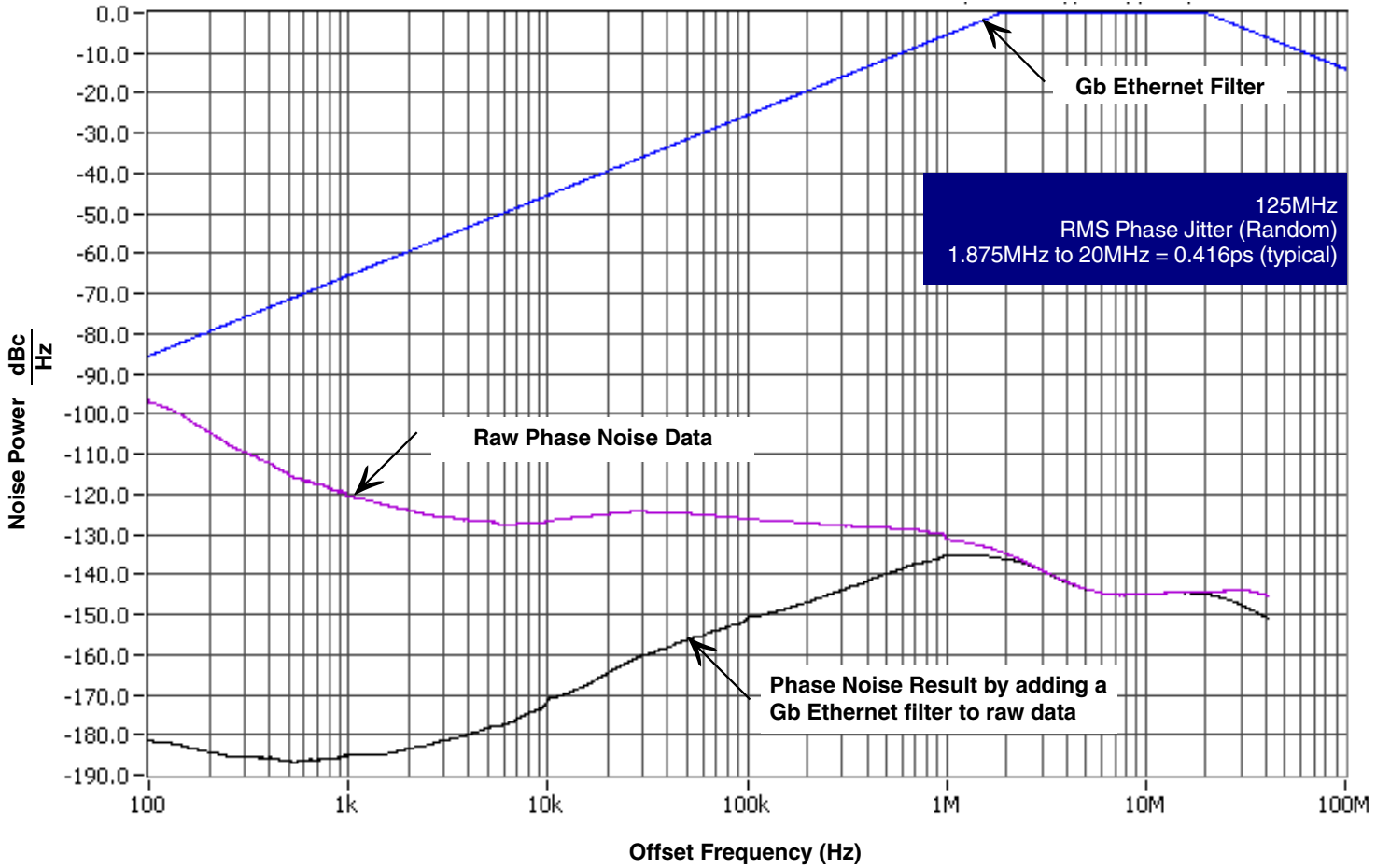
NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: See Phase Noise Plot.

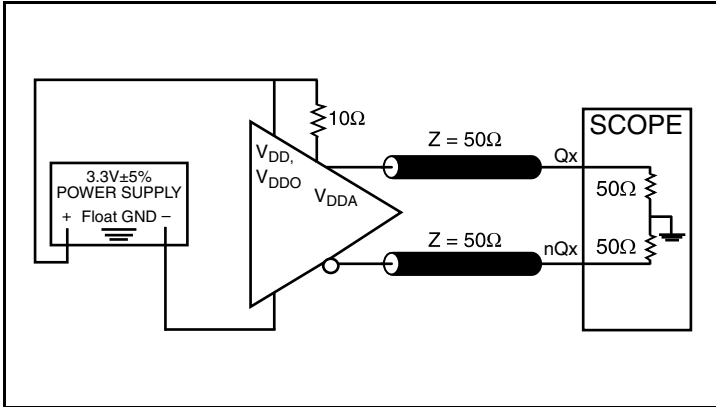
NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

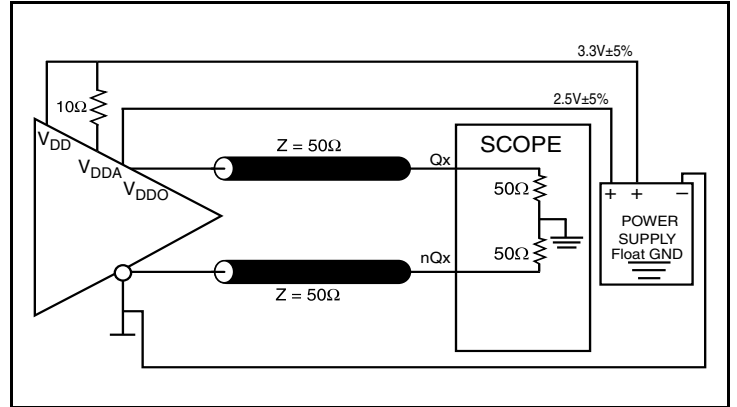
Typical Phase Noise at 125MHz



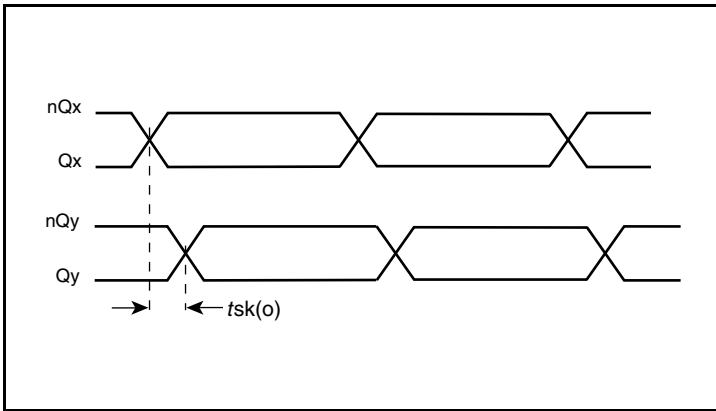
Parameter Measurement Information



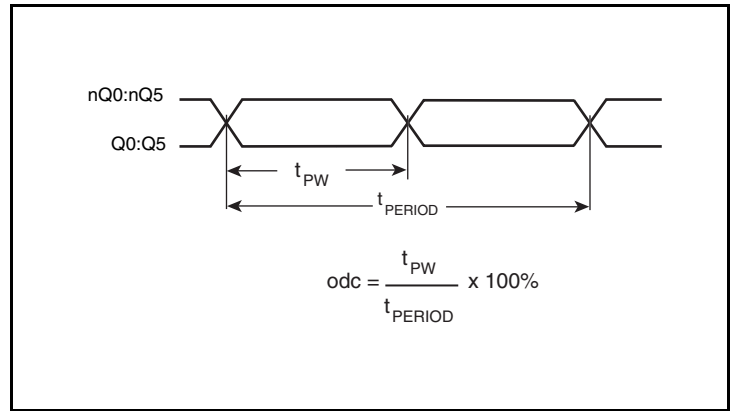
3.3V Core/3.3V LVDS Output Load AC Test Circuit



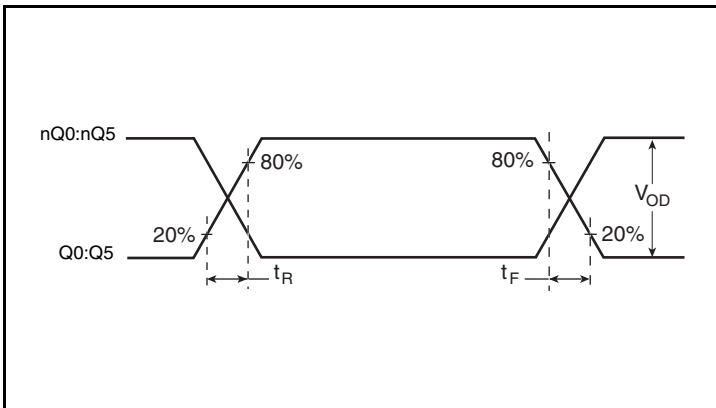
3.3V Core/2.5V LVDS Output Load AC Test Circuit



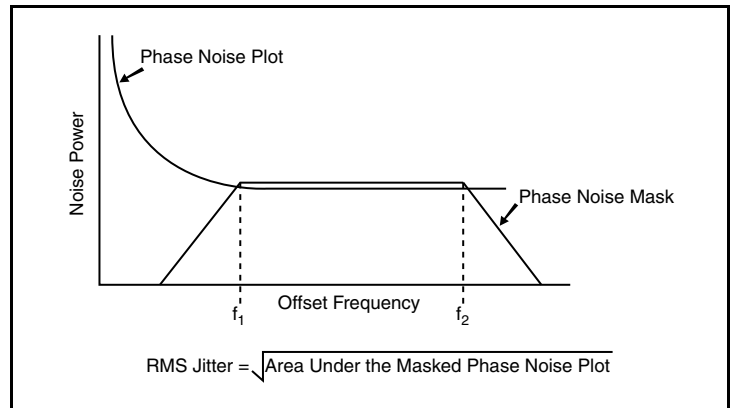
Output Skew



Output Duty Cycle/Pulse Width/Period

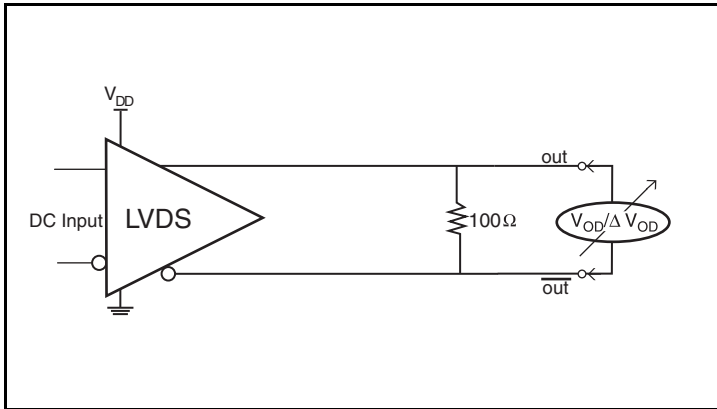


Output Rise/Fall Time

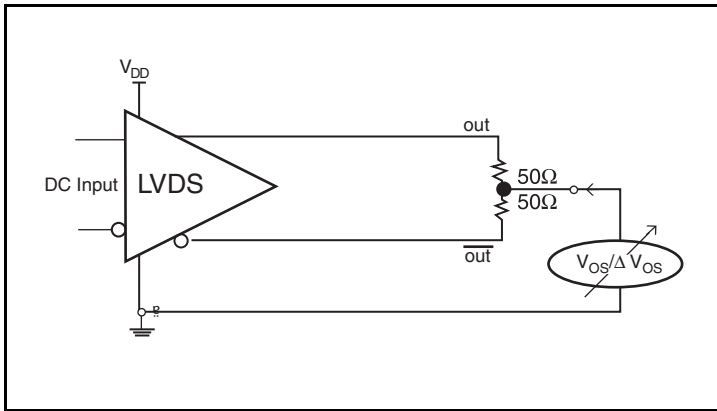


RMS Phase Jitter

Parameter Measurement Information, continued



Differential Output Voltage Setup



Offset Voltage Setup

Applications Information

Overdriving the XTAL Interface

The XTAL_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. *Figure 1A* shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (R_o) and the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This

can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω. This can also be accomplished by removing R_1 and changing R_2 to 50Ω. The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. *Figure 1B* shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.

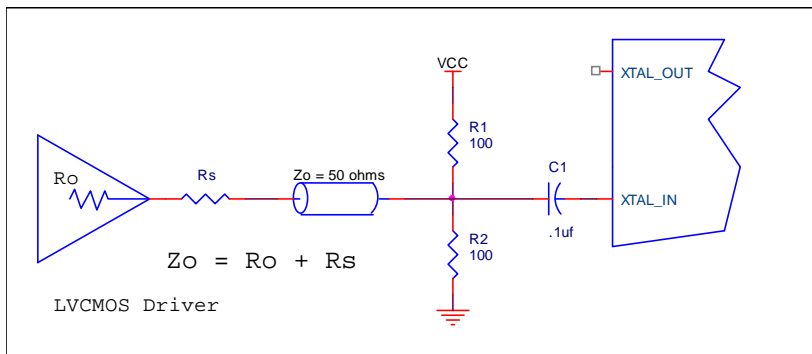


Figure 1A. General Diagram for LVCMOS Driver to XTAL Input Interface

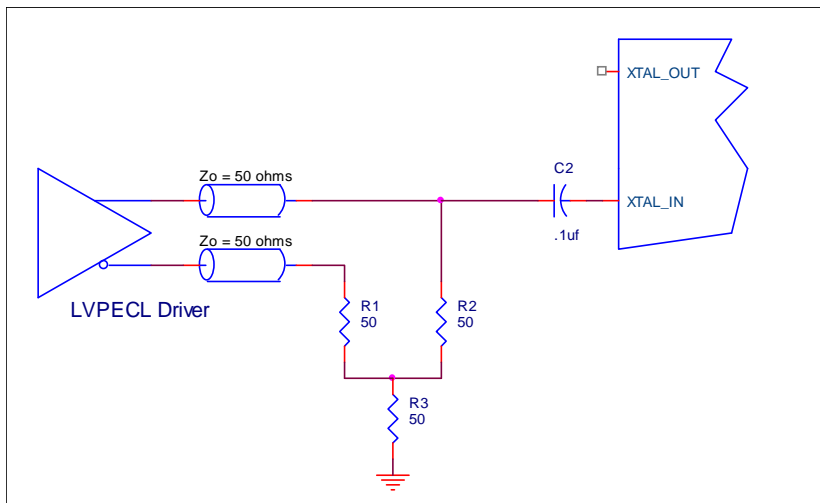


Figure 1B. General Diagram for LVPECL Driver to XTAL Input Interface

Recommendations for Unused Input and Output Pins

Inputs:

LVCMOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

Outputs:

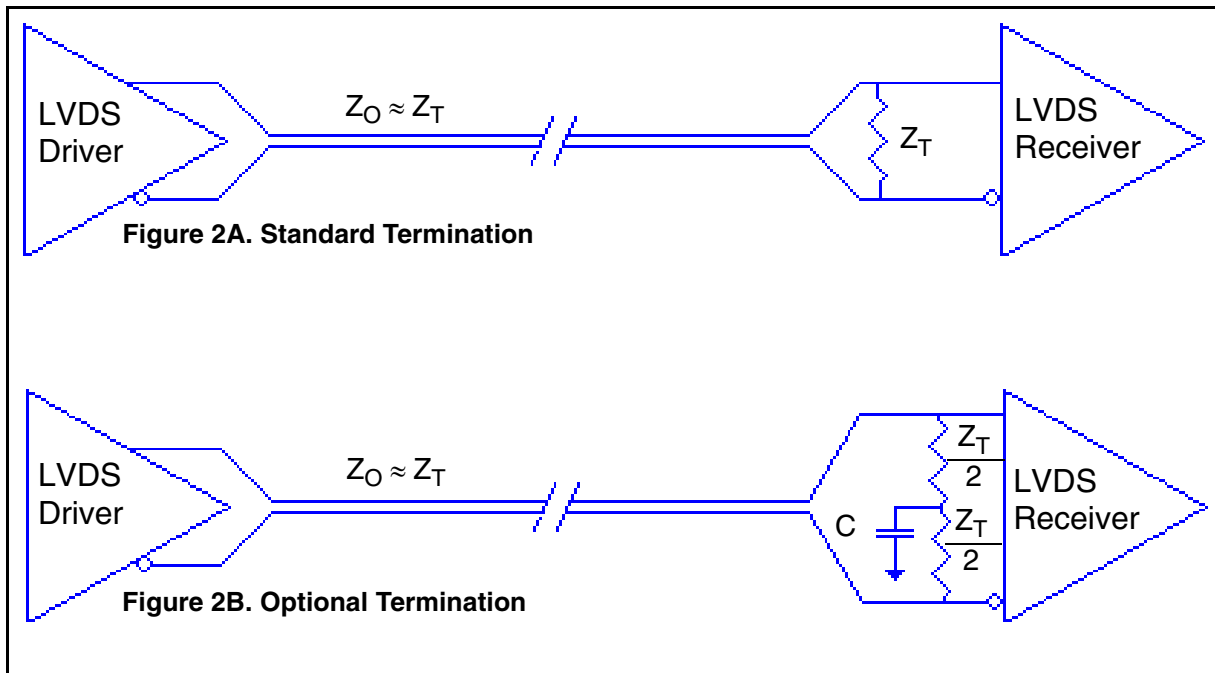
LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached.

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90Ω and 132Ω. The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100Ω parallel resistor at the receiver and a 100Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard termination

schematic as shown in *Figure 2A* can be used with either type of output structure. *Figure 2B*, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.



LVDS Termination

EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 3*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific and

dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, refer to the Application Note on the *Surface Mount Assembly* of Amkor’s Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.

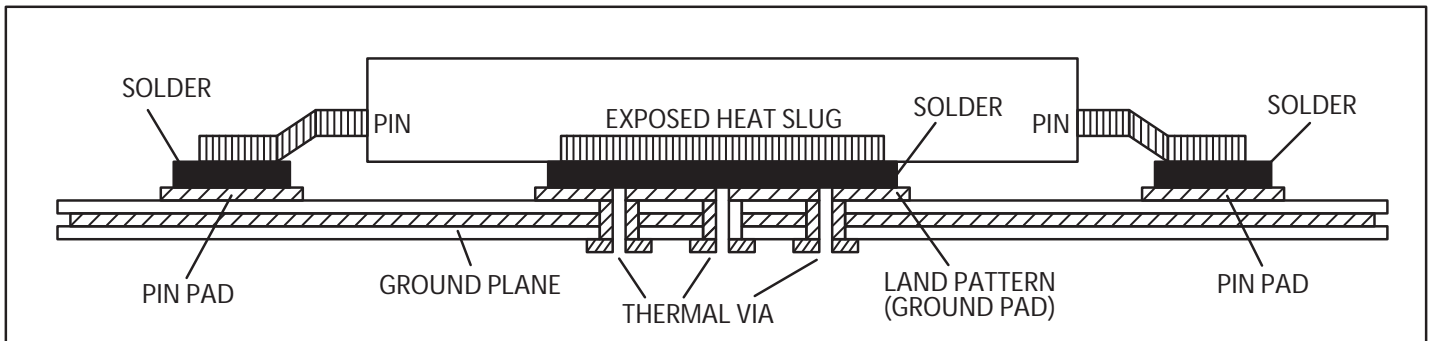


Figure 3. Assembly for Exposed Pad Thermal Release Path - Side View (drawing not to scale)

Schematic Layout

Figure 4 shows an example of ICS844246DI-08 application schematic. The schematic example focuses on functional connections and is not configuration specific. Refer to the pin description and functional tables in the datasheet to ensure the logic control inputs are properly set. Input and output terminations shown are intended as examples only and may not represent the exact user configuration.

In this example an 18pF parallel resonant 25MHz crystal is used with load caps $C7 = C6 = 22\text{pF}$. The load caps are recommended for frequency accuracy, but these may be adjusted for different board layouts. Crystals with different load capacities may be used, but the load capacitors will have to be changed accordingly. If different crystal types are used, please consult IDT for recommendations.

The schematic example shows two different LVDS output terminations; the standard termination 100Ω shunt termination for an LVDS compliant receiver and an AC coupled termination for a non-LVDS differential receiver. The AC coupled termination requires that the designer select the values of R4 and R6 in order to center the LVDS swing within the common mode range of the receiver. In addition the designer must make sure that the target receiver will operate reliably with the LVDS swing, which is reduced relative to other logic families such as HCSL or LVPECL.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The ICS844246DI provides separate V_{DD} , V_{DDA} and V_{DDO} pins to isolate any high speed switching noise at the outputs from coupling into the internal PLL.

In order to achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB as close to the power pins as possible. If space is limited, the 0.1uF capacitor in each power pin filter should be placed on the device side of the PCB and the other components can be placed on the opposite side.

Power supply filter recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10kHz. If a specific frequency noise component is known, such as switching power supply frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally, good general design practices for power plane voltage stability suggests adding bulk capacitances in the local area of all devices.

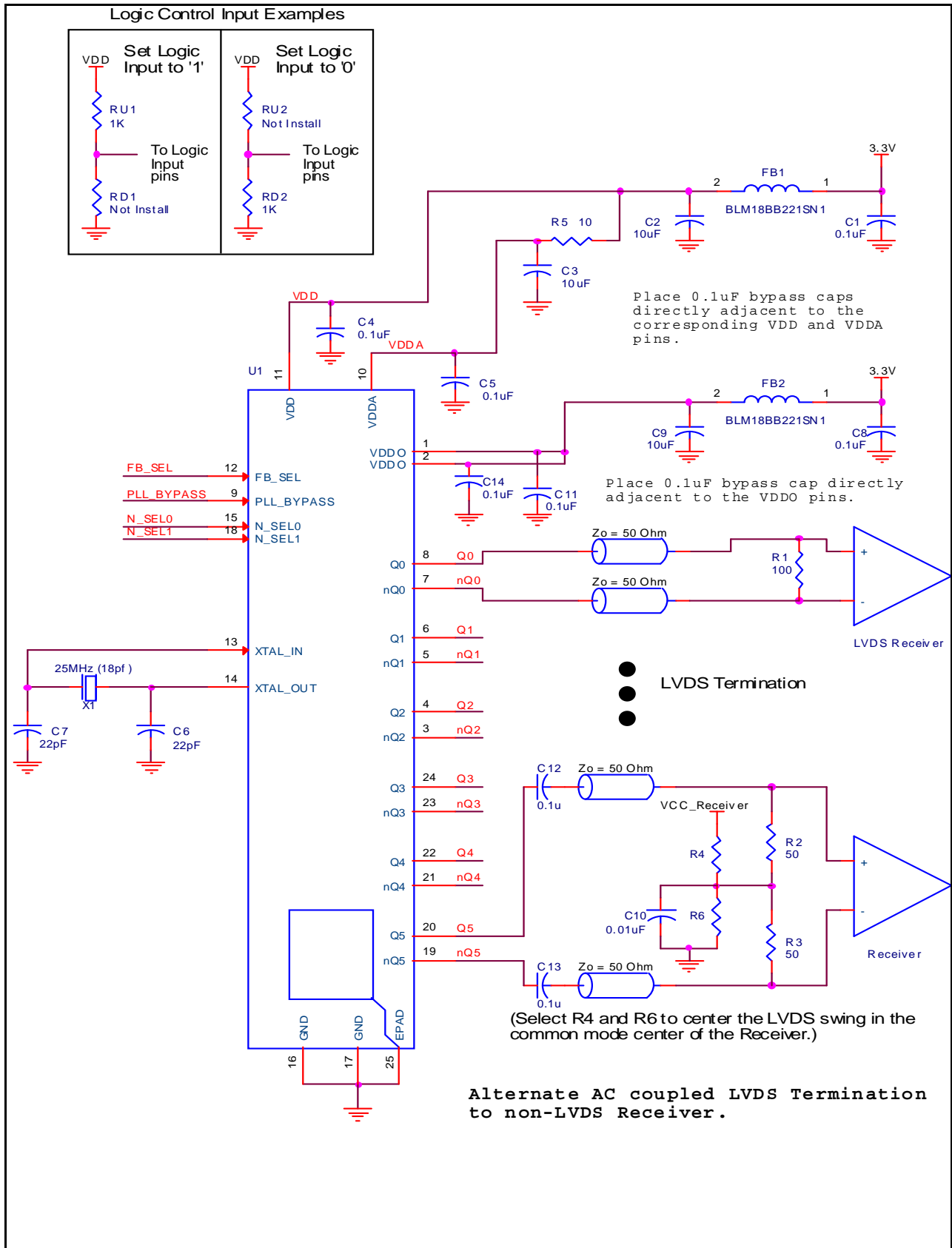


Figure 4. ICS844246DI Application Schematic

Power Considerations

This section provides information on power dissipation and junction temperature for the ICS844246DI. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS844246DI is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{DD_MAX} * (I_{DD_MAX} + I_{DDA_MAX}) = 3.465V * (170mA + 10mA) = \mathbf{623.7mW}$
- Power (outputs)_{MAX} = $V_{DDO_MAX} * I_{DDO_MAX} = 3.465V * 100mA = \mathbf{346.5mW}$

Total Power_{MAX} = 623.7mW + 346.5mW = 970.2mW

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 32.1°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ\text{C} + 0.970\text{W} * 32.1^\circ\text{C/W} = 116.1^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 7. Thermal Resistance θ_{JA} for 24 Lead TSSOP, E-Pad Forced Convection

| θ_{JA} by Velocity | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 32.1°C/W | 25.5°C/W | 24.0°C/W |

Reliability Information

Table 8. θ_{JA} vs. Air Flow Table for a 24 Lead TSSOP, E-Pad

| θ_{JA} vs. Air Flow | | | |
|---|----------|----------|----------|
| Meters per Second | 0 | 1 | 2.5 |
| Multi-Layer PCB, JEDEC Standard Test Boards | 32.1°C/W | 25.5°C/W | 24.0°C/W |

Transistor Count

The transistor count for ICS844246DI is: 3887

Package Outline and Package Dimensions

Package Outline - G Suffix for 24 Lead TSSOP, E-Pad

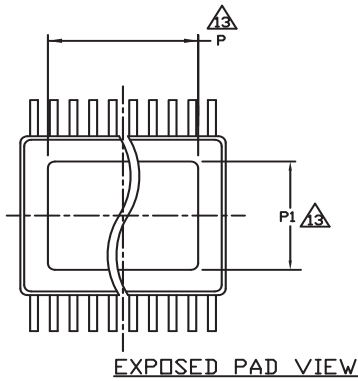
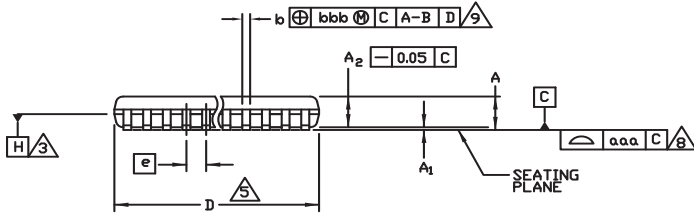
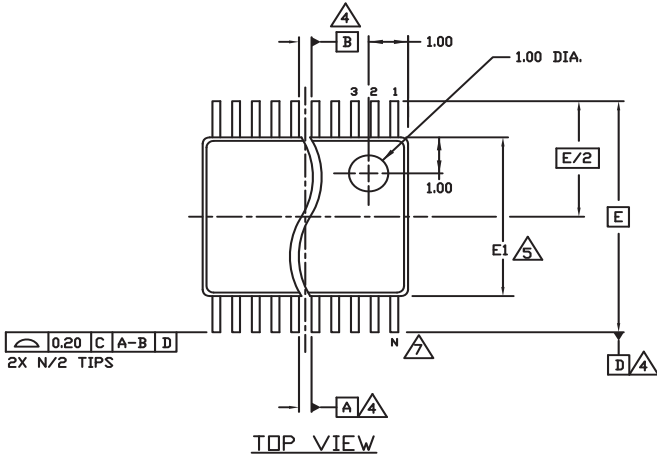
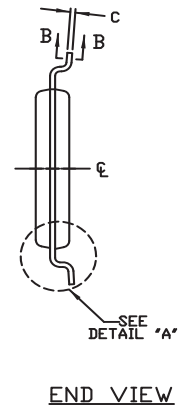
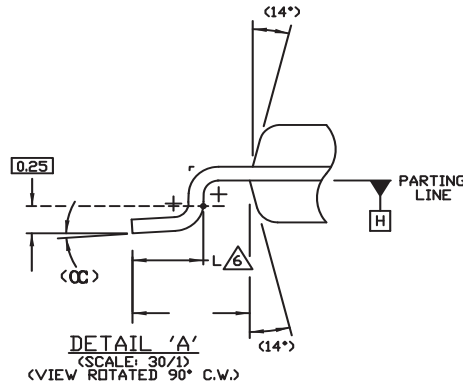
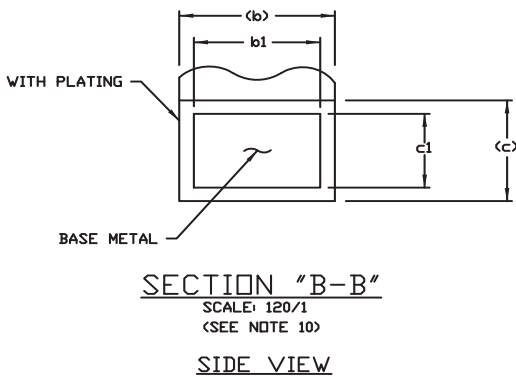
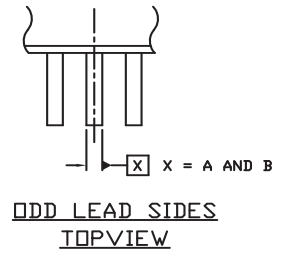
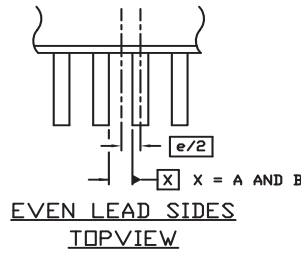


Table 9. Package Dimensions for 24 Lead TSSOP, E-Pad)

| All Dimensions in Millimeters | | | |
|-------------------------------|------------|---------|---------|
| Symbol | Minimum | Nominal | Maximum |
| N | 24 | | |
| A | | | 1.10 |
| A1 | 0.05 | | 0.15 |
| A2 | 0.85 | 0.90 | 0.95 |
| b | 0.19 | | 0.30 |
| b1 | 0.19 | 0.22 | 0.25 |
| c | 0.09 | | 0.20 |
| c1 | 0.09 | 0.127 | 0.16 |
| D | 7.70 | | 7.90 |
| E | 6.40 Basic | | |
| E1 | 4.30 | 4.40 | 4.50 |
| e | 0.65 Basic | | |
| L | 0.50 | 0.60 | 0.70 |
| P | 5.0 | | 5.5 |
| P1 | 3.0 | | 3.2 |
| α | 0° | | 8° |
| $\alpha\alpha\alpha$ | 0.076 | | |
| bbb | 0.10 | | |

Reference Document: JEDEC Publication 95, MO-153



Ordering Information

Table 10. Ordering Information

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|---------------|----------------------------------|--------------------|---------------|
| 844246DGILF | ICS844246DGIL | "Lead-Free" 24 Lead TSSOP, E-Pad | Tube | -40°C to 85°C |
| 844246DGILFT | ICS844246DGIL | "Lead-Free" 24 Lead TSSOP, E-Pad | Tape & Reel | -40°C to 85°C |

Revision History Sheet

| Rev | Table | Page | Description of Change | Date |
|-----|-------|------|---|------------|
| A | | 7 | Phase Noise Plot - corrected font arrow characters. | 11/28/2012 |
| | | | | |

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